

INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)				Docket Number (Optional) YOR919990509US3 (13171AB)		Application Number Unassigned 10/827064	
				Applicant(s) Cyril Cabral, Jr., et al.			
				Filing Date Herewith 4/19/04		Group Art Unit Unassigned 2813	
				U.S. PATENT DOCUMENTS			
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
EK		5,510,295	4/23/96	Cabral, Jr., et al.	—	—	
		5,608,226	3/4/97	Yamada, et al.	—	—	
		5,624,869	4/29/97	Agnello, et al.	—	—	
		5,828,131	10/27/98	Cabral, Jr., et al.	—	—	
		5,830,775	11/1998	Maa, et al.	—	—	
		5,710,450	1/1998	Chau, et al.	—	—	
		6,121,100	9/2000	Andideh, et al.	—	—	
		6,165,826	12/2000	Chau, et al.	—	—	
		6,211,560 B1	4/2001	Jimenez, et al.	—	—	
		6,326,664 B1	12/2001	Chau, et al.	—	—	
FOREIGN PATENT DOCUMENTS							
REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
EK	M. Lawrence, et al., "Growth of Epitaxial CoSi ₂ on (100) Si, "Appl. Phys. Lett., Vol. 58, No. 12, pp. 1308-1310 (1991).						
EK	Wolf, Silicon Processing for the VLSI Era, Vol. 2-Process Intergration, Lattice Press: Sunset Beach CA, 1990, pp. 144-151.						
EK	C. Cabral, et al., "In-Situ X-Ray Diffractin and Resistivity Analysis of CoSi ₂ Phase Formation With and Without a Ti Interlayer at Rapid Thermal Annealing Rates, "Mat. Res. Soc. Symp. Proc., Vol. 375, pp. 253-258 (1995).						
EXAMINER <i>EK</i>	DATE CONSIDERED <i>12/11/2004</i>						
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

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